

N-Channel 40 V (D-S) Super Junction MOSFET

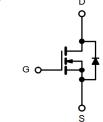
PRODUCT SUMMARY						
V _{DS} (V)	R _{DS(on)} (mΩ) (TYP.)	I _D (A) ^{a,e}	Q _g (TYP.)			
40	0.58 at V _{GS} = 10 V	245	98 nC			

FEATURES

- · DT-SJ Power MOSFET
- 100 % R_g and UIS Tested
- AEC-Q101 Qualified for **Automotive Applications**

APPLICATIONS

- · Notebook PC Core
- VRM/POL

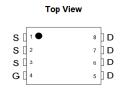




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DFN5*6 Double Cooling



ABSOLUTE MAXIMUM RATINGS	(T _A = 25 °C, unle	ess otherwise r	noted)		
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	40	V	
Gate-Source Voltage		V_{GS}	± 20		
	T _C = 25 °C		245 ^{a,e}		
Continuous Drain Current (T _J = 175 °C)	T _C =70 °C		218		
Continuous Drain Current (1) = 173 C)	T _A = 25 °C	I _D	60 ^{b, c}	A	
	T _A = 70 °C		40 ^{b, c}		
Pulsed Drain Current		I _{DM}	920		
Avalanche Current Pulse	L = 0.1 mH	I _{AS}	230		
Single Pulse Avalanche Energy	L = 0.1 IIII	E _{AS}	956	mJ	
Continuous Source-Drain Diode Current	T _C = 25 °C	I _S	245 ^a	A	
Continuous Source-Drain Diode Current	T _A = 25 °C	'S	60 ^{b, c}		
	T _C = 25 °C		376 ^a		
Manipular Davida Disabatian	T _C = 70 °C	P _D	241	\Box w	
Maximum Power Dissipation	T _A = 25 °C	' D	56 ^{b, c}	vv	
	T _A = 70 °5		40 ^{b, c}		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 s	R _{thJA}	1.5	2.7	°C/W
Maximum Junction-to-Case	Steady State	R _{thJC}	0.25	0.39	O/ VV

- a. Based on T_C = 25 °C. b. Surface mounted on 1" x 1" FR4 board.
- d. Calculated based on maximum junction temperature.
- e. Package limited.

Rev. 1.0 1





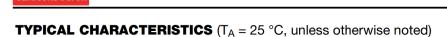
Parameter	Symbol	Test Conditions	Min .	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V, } I_{D} = 250 \mu\text{A}$	40			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		25		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	ι _D – 200 μΑ		- 6.2		l mv/ C	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.5		3.5	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zoro Coto Valtago Drain Current	1	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}$			1	········ uA	
Zero Gate Voltage Drain Current	DSS	$V_{DS} = 32 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	240			Α	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$		0.58	0.69	mΩ	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 5 \text{ V}, I_{D} = 30 \text{ A}$		122		S	
Dynamic ^b							
Input Capacitance	C _{iss}			6650		pF	
Output Capacitance	C _{oss}	V_{DS} = 20 V, V_{GS} = 0 V, f = 1 MHz		2100			
Reverse Transfer Capacitance	C _{rss}			185			
Total Gate Charge	Qg			98		nC	
Gate-Source Charge	Q _{gs}	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 30 \text{ A}$		19			
Gate-Drain Charge	Q _{gd}			13			
Gate Resistance	R _g	f = 1 MHz		1.5		Ω	
Turn-On Delay Time	t _{d(on)}			22			
Rise Time	t _r	V_{DD} = 15 V, R_L = 0.555 Ω		10		ns	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 30A$, $V_{GEN} = 10 \text{ V}$, $R_g = 1 \Omega$		62			
Fall Time	t _f			10			
Drain-Source Body Diode Characteristic	s						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			245	_	
Pulse Diode Forward Current ^a	I _{SM}				920	A	
Body Diode Voltage	V _{SD}	I _S = 1 A		0.6	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			26		ns	
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = 30 A, di/dt = 100 A/μs, T _J = 25 °C		88		nC	
Reverse Recovery Fall Time	t _a	i _F = 30 A, αl/αι = 100 A/μs, 1 _J = 25 C		26		ns	
Reverse Recovery Rise Time	t _b			23			

Notes:

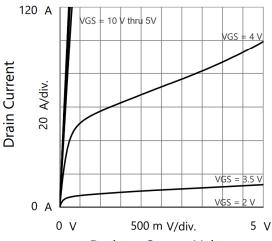
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

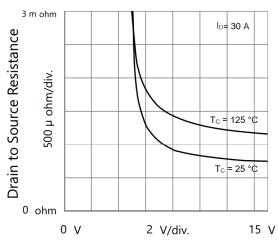


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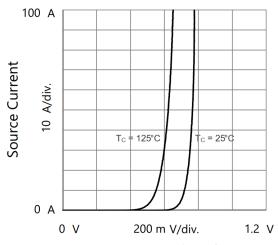


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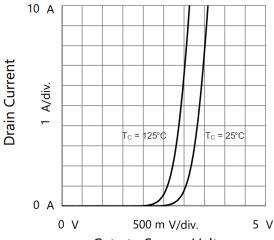
Drain to Source Voltage Output Characteristics



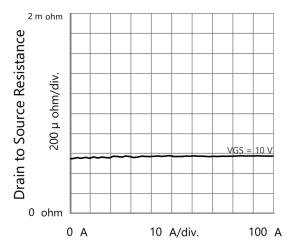
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



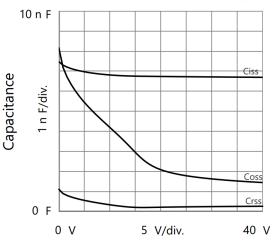
Source to Drain Voltage Body Diode Forward Characteristics



Gate to Source Voltage Transfer Characteristics



Drain Current
Drain to Source Resistance vs. Drain Current

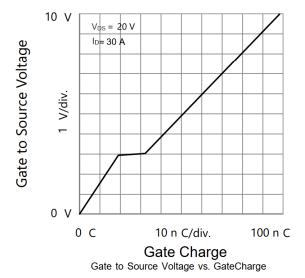


Drain to Source Voltage Capacitances

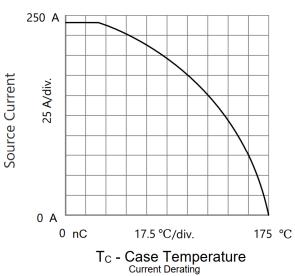


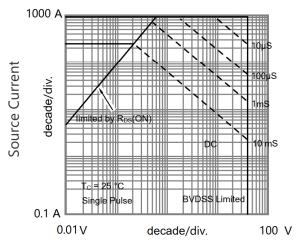
WUT 1000 Q

TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

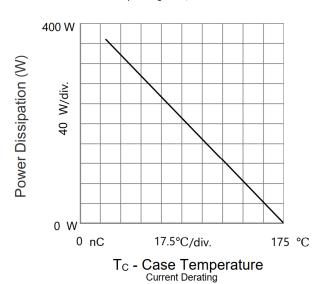


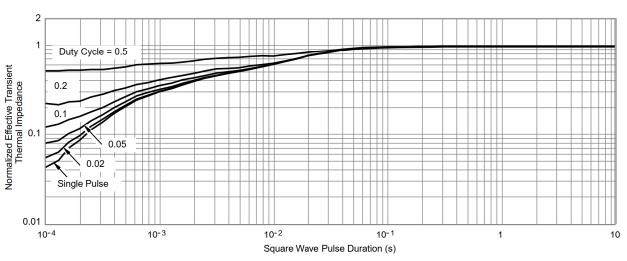
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Source to Drain Voltage Safe Operating Area, Junction-to-Ambient

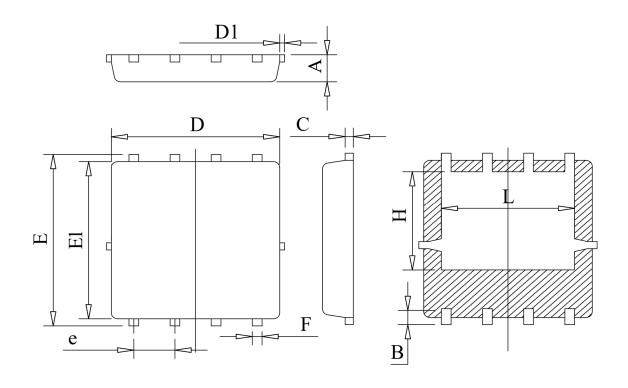




Normalized Thermal Transient Impedance, Junction-to-Case



DFN5X6-8L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Unit: mm

Symbol	Min	Тур	Max
A	0.78	0.95	1.12
В	0.45	0.58	0.78
С	0.18	0.254	0.36
D	4.70	5.20	5.45
D1			0.18
Е	5.85	6.05	6.25
E1	5.38	5.55	5.98
e	1.15	1.27	1.40
F	0.18	0.30	0.52
Н	3.25	3.47	3.70
L	3.75	4.00	4.25

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